

PC3Q410NIP0F

*1-channel package type is also available.
(model No. **PC3H41xNIP0F Series**)

Mini-flat Half Pitch 4-channel Package, High CMR, AC Input, Low Input Current Photocoupler



■ Description

PC3Q410NIP0F contains a IRED optically coupled to a phototransistor.

It is packaged in a 4 channel Mini-flat, half pitch type.

Input-output isolation voltage(rms) is 2.5kV.

Collector-emitter Voltage is 80V, CTR is 50% to 400% at input current of $\pm 0.5\text{mA}$ and CMR is MIN. $10\text{kV}/\mu\text{s}$.

■ Features

1. 4-channel Mini-flat Half pitch package (Lead pitch : 1.27mm)
2. Double transfer mold package (Ideal for Flow Soldering)
3. AC input type
4. Low input current type ($I_F = \pm 0.5\text{mA}$)
5. High collector-emitter voltage ($V_{CEO} : 80\text{V}$)
6. High noise immunity due to high common mode rejection voltage (CMR : MIN. $10\text{kV}/\mu\text{s}$)
7. Isolation voltage between input and output ($V_{iso(rms)} : 2.5\text{kV}$)
8. Lead-free and RoHS directive compliant

■ Agency approvals/Compliance

1. Recognized by UL1577 (Double protection isolation), file No. E64380 (as model No. **PC3Q41**)
2. Package resin : UL flammability grade (94V-0)

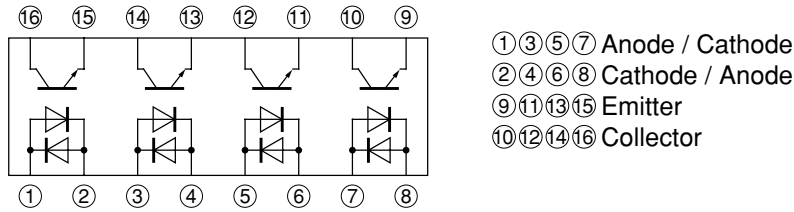
■ Applications

1. Programmable controllers
2. Facsimiles
3. Telephones

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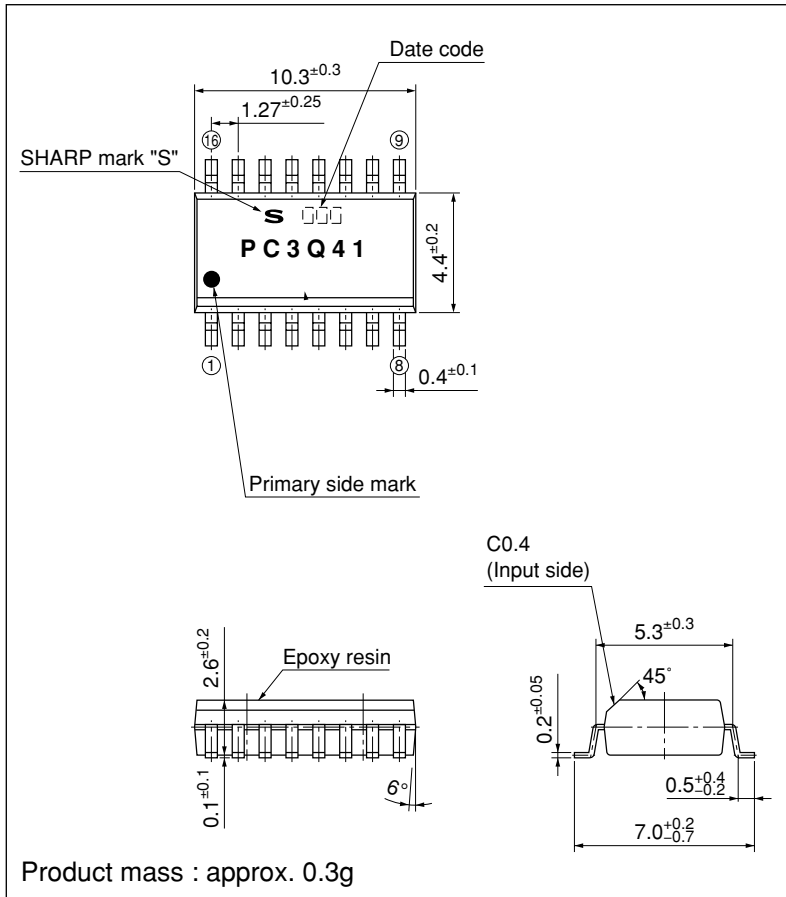
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■ Internal Connection Diagram



■ Outline Dimensions

(Unit : mm)



Plating material : SnCu (Cu : TYP. 2%)

Date code (3 digit)

1st digit				2nd digit		3rd digit	
Year of production				Month of production		Week of production	
A.D.	Mark	A.D	Mark	Month	Mark	Week	Mark
1990	A	2002	P	January	1	1st	1
1991	B	2003	R	February	2	2nd	2
1992	C	2004	S	March	3	3rd	3
1993	D	2005	T	April	4	4th	4
1994	E	2006	U	May	5	5, 6th	5
1995	F	2007	V	June	6		
1996	H	2008	W	July	7		
1997	J	2009	X	August	8		
1998	K	2010	A	September	9		
1999	L	2011	B	October	O		
2000	M	2012	C	November	N		
2001	N	∴	∴	December	D		

repeats in a 20 year cycle

Country of origin

Japan

Rank mark

There is no rank mark indicator.

■ Absolute Maximum Ratings (T_a=25°C)

	Parameter	Symbol	Rating	Unit
Input	Forward current	I _F	±10	mA
	*1 Peak forward current	I _{FM}	±200	mA
	Power dissipation	P	15	mW
Output	Collector-emitter voltage	V _{CEO}	80	V
	Emitter-collector voltage	V _{ECO}	6	V
	Collector current	I _C	50	mA
	Collector power dissipation	P _C	150	mW
	Total power dissipation	P _{tot}	170	mW
	Operating temperature	T _{opr}	-30 to +100	°C
	Storage temperature	T _{stg}	-40 to +125	°C
	*2 Isolation voltage	V _{iso (rms)}	2.5	kV
	*3 Soldering temperature	T _{sol}	260	°C

*1 Pulse width ≤ 100μs, Duty ratio : 0.001

*2 40 to 60%RH, AC for 1 minute, f=60Hz

*3 For 10s

■ Electro-optical Characteristics (T_a=25°C)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input	Forward voltage	V _F	I _F =±5mA	-	1.2	1.4	V	
	Terminal capacitance	C _t	V=0, f=1kHz	-	30	250	pF	
Output	Collector dark current	I _{CEO}	V _{CE} =50V, I _F =0	-	-	100	nA	
	Collector-emitter breakdown voltage	BV _{CEO}	I _C =0.1mA, I _F =0	80	-	-	V	
	Emitter-collector breakdown voltage	BV _{ECO}	I _E =10μA, I _F =0	6	-	-	V	
Transfer characteristics	Collector current	I _C	I _F =±0.5mA, V _{CE} =5V	0.25	-	2.0	mA	
	Collector-emitter saturation voltage	V _{CE (sat)}	I _F =±10mA, I _C =1mA	-	-	0.2	V	
	Isolation resistance	R _{ISO}	DC500V, 40 to 60%RH	5×10 ¹⁰	1×10 ¹¹	-	Ω	
	Floating capacitance	C _f	V=0, f=1MHz	-	0.6	1.0	pF	
	Response time	Rise time	t _r	V _{CE} =2V, I _C =2mA, R _L =100Ω	-	4	18	μs
		Fall time	t _f		-	3	18	μs
	Common mode rejection voltage	CMR	T _a =25°C, R _L =470Ω, V _{CM} =1.5kV(peak), I _F =0, V _{CC} =9V, V _{np} =100mV	10	-	-	kV/μs	

Fig.1 Test Circuit for Common Mode Rejection Voltage

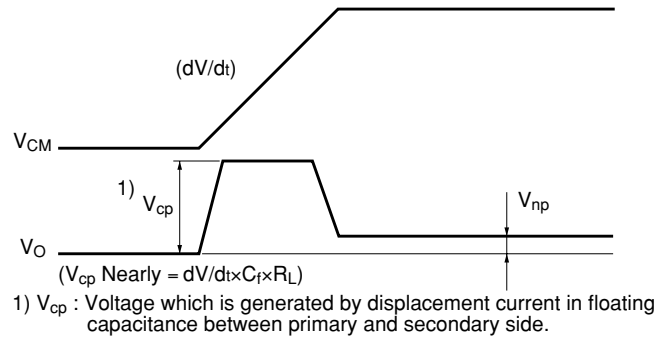
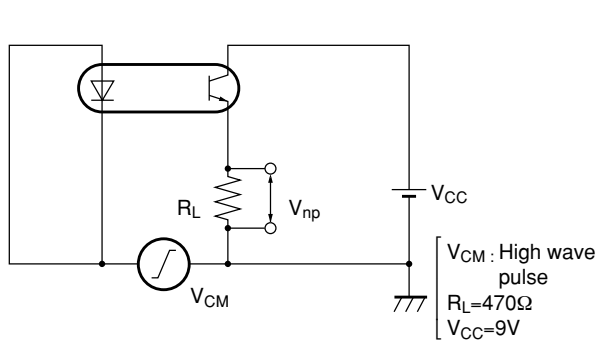


Fig.2 Forward Current vs. Ambient Temperature

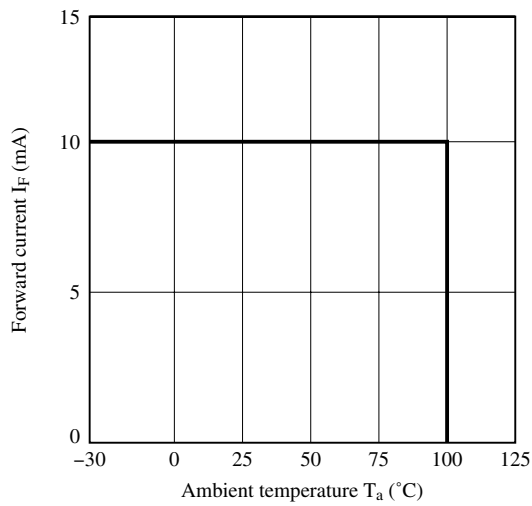


Fig.3 Diode Power Dissipation vs. Ambient Temperature

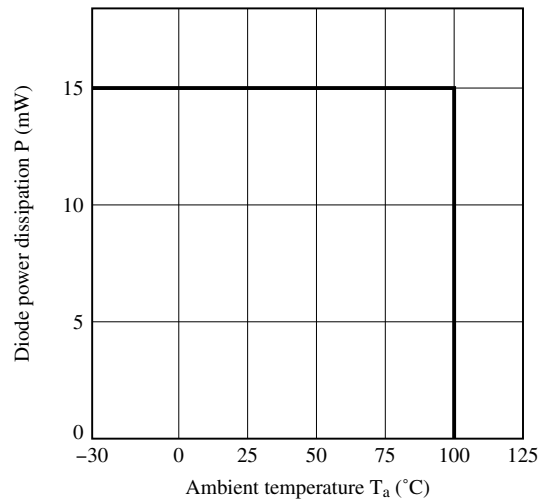


Fig.4 Collector Power Dissipation vs. Ambient Temperature

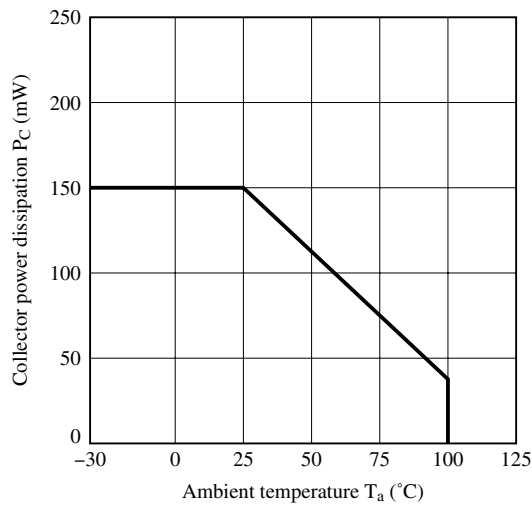


Fig.5 Total Power Dissipation vs. Ambient Temperature

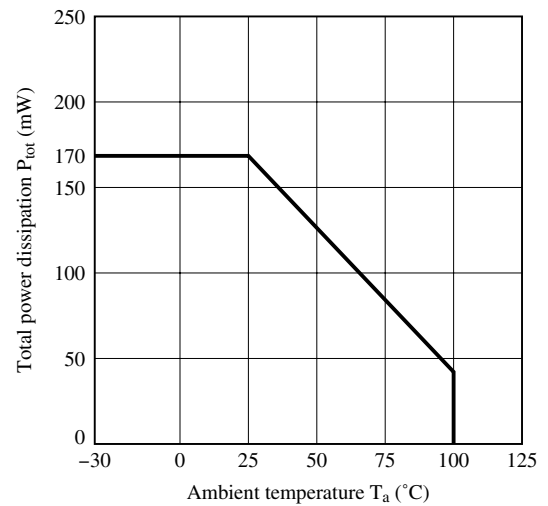


Fig.6 Peak Forward Current vs. Duty Ratio

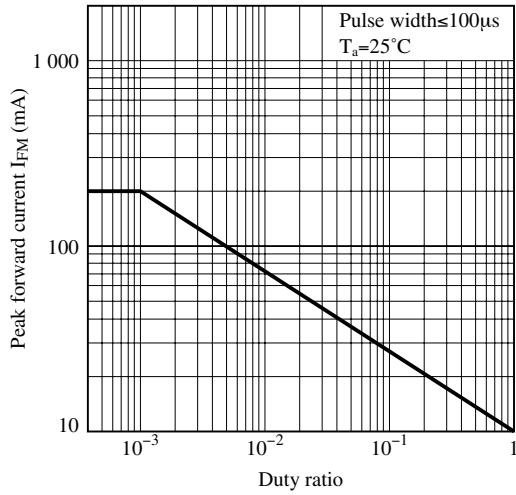


Fig.7 Forward Current vs. Forward Voltage

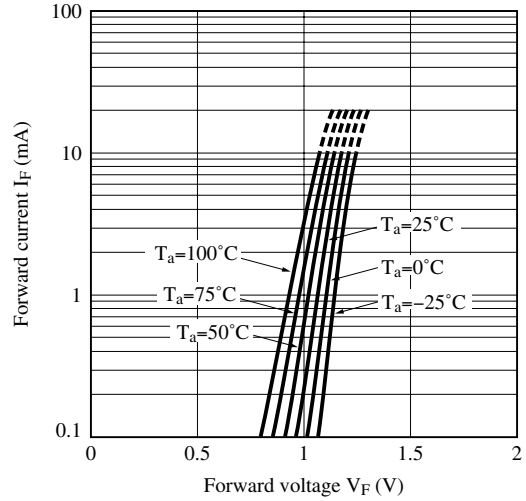


Fig.8 Current Transfer Ratio vs. Forward Current

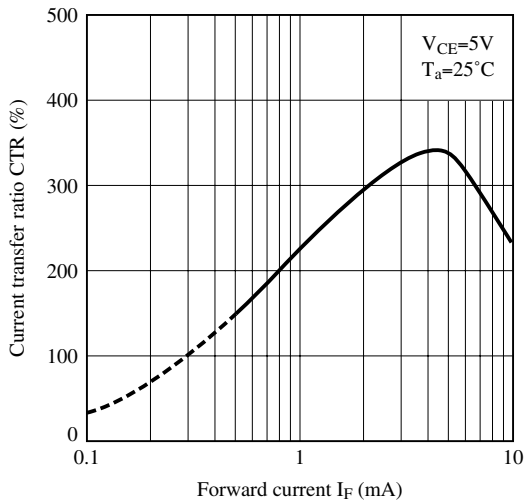


Fig.9 Collector Current vs. Collector-emitter Voltage

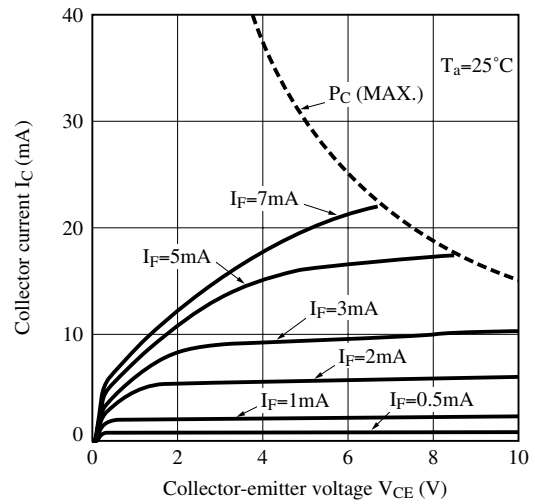


Fig.10 Relative Current Transfer Ratio vs. Ambient Temperature

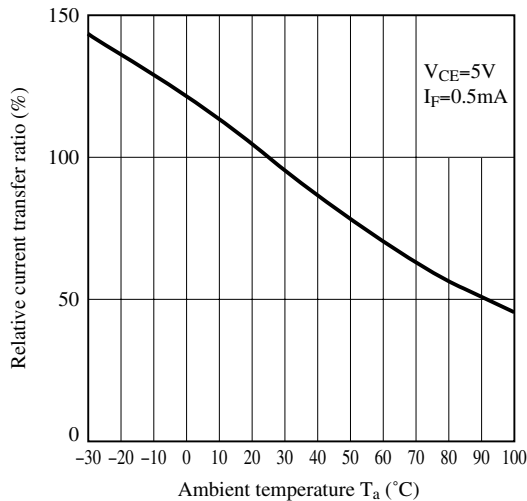


Fig.11 Collector - emitter Saturation Voltage vs. Ambient Temperature

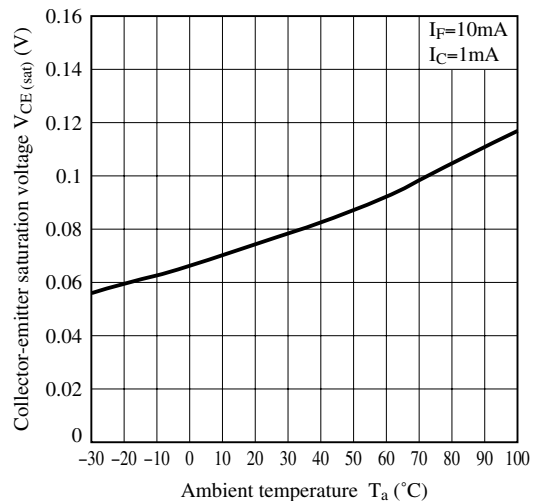


Fig.12 Collector Dark Current vs. Ambient Temperature

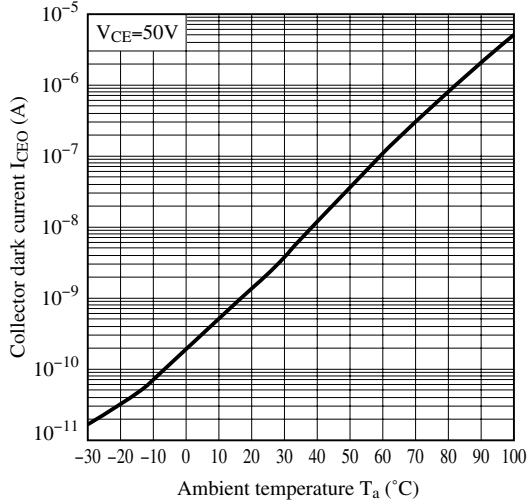


Fig.13 Response Time vs. Load Resistance (active region)

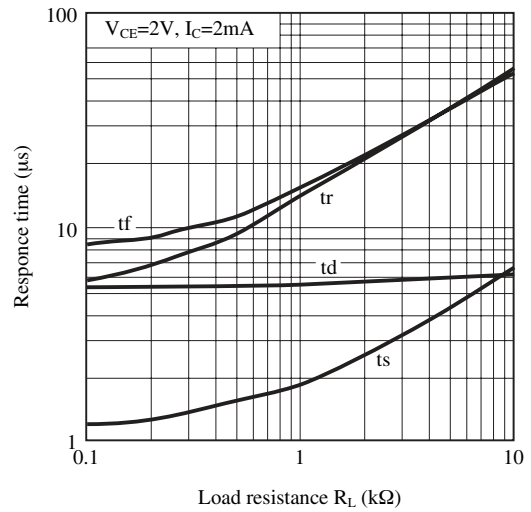


Fig.14 Response Time vs. Load Resistance (saturation region)

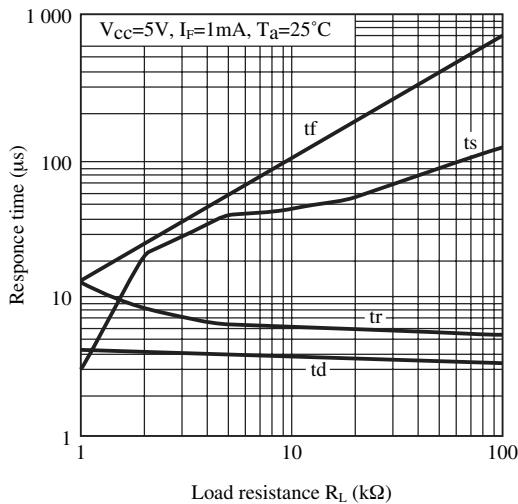
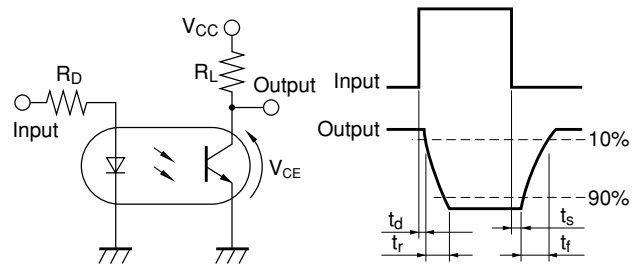


Fig.15 Test Circuit for Response Time



Please refer to the conditions in Fig.13 and Fig.14

Fig.16 Frequency Response

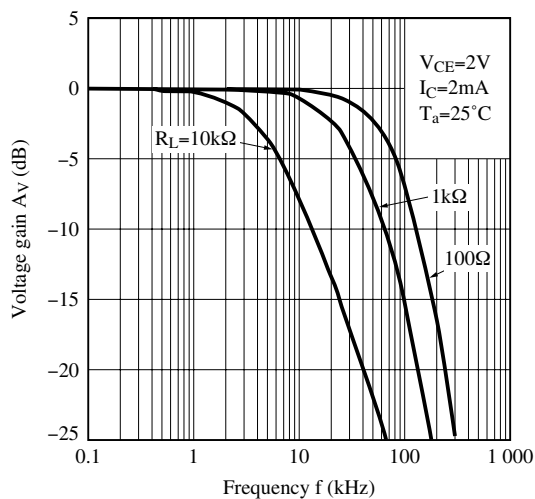
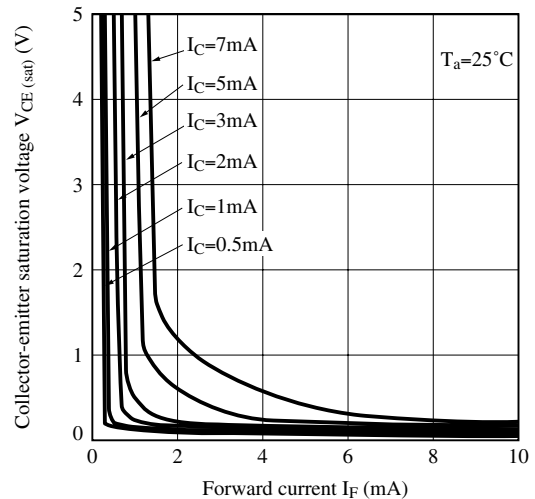


Fig.17 Collector-emitter Saturation Voltage vs. Forward Current



Remarks : Please be aware that all data in the graph are just for reference and not for guarantee.

■ Design Considerations

● Design guide

While operating at $I_F < 0.5\text{mA}$, CTR variation may increase.
Please make design considering this fact.

In case that some sudden big noise caused by voltage variation is provided between primary and secondary terminals of photocoupler some current caused by it is floating capacitance may be generated and result in false operation since current may go through IRED or current may change.

If the photocoupler may be used under the circumstances where noise will be generated we recommend to use the bypass capacitors at the both ends of IRED.

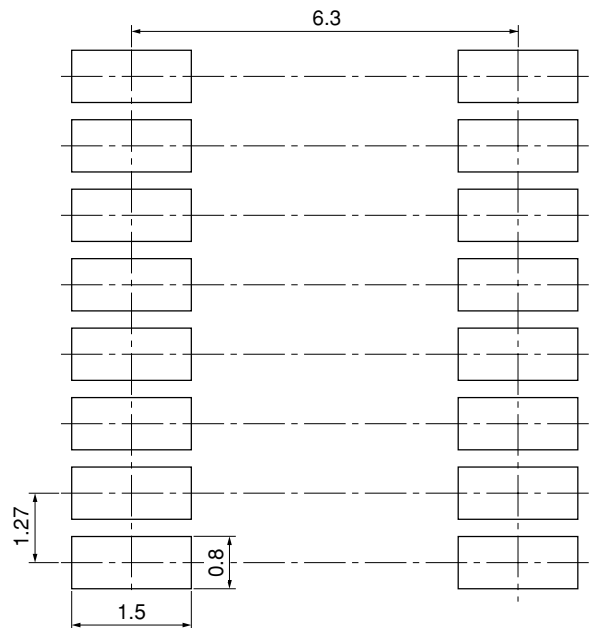
This product is not designed against irradiation and incorporates non-coherent IRED.

● Degradation

In general, the emission of the IRED used in photocouplers will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

● Recommended Foot Print (reference)



(Unit : mm)

☆ For additional design assistance, please review our corresponding Optoelectronic Application Notes.

■ Manufacturing Guidelines

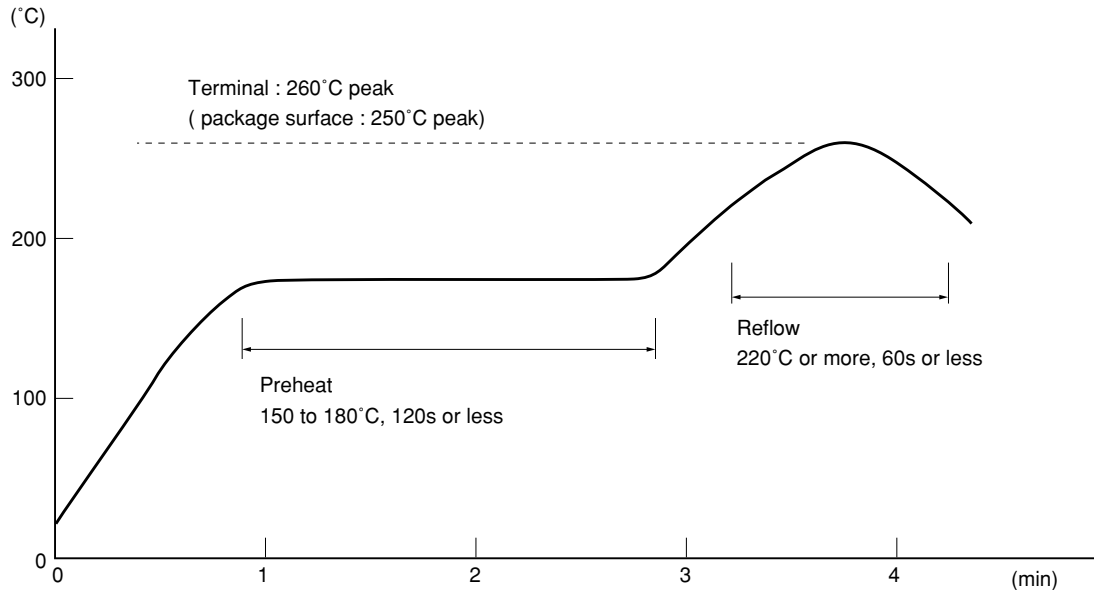
● Soldering Method

Reflow Soldering:

Reflow soldering should follow the temperature profile shown below.

Soldering should not exceed the curve of temperature profile and time.

Please don't solder more than twice.



Flow Soldering :

Due to SHARP's double transfer mold construction submersion in flow solder bath is allowed under the below listed guidelines.

Flow soldering should be completed below 260°C and within 10s.

Preheating is within the bounds of 100 to 150°C and 30 to 80s.

Please don't solder more than twice.

Hand soldering

Hand soldering should be completed within 3s when the point of solder iron is below 400°C.

Please don't solder more than twice.

Other notices

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.

● Cleaning instructions**Solvent cleaning:**

Solvent temperature should be 45°C or below Immersion time should be 3 minutes or less

Ultrasonic cleaning:

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol

In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

● Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this product.

Regulation substances : CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).

- Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).

■ **Package specification**

● **Tape and Reel package**

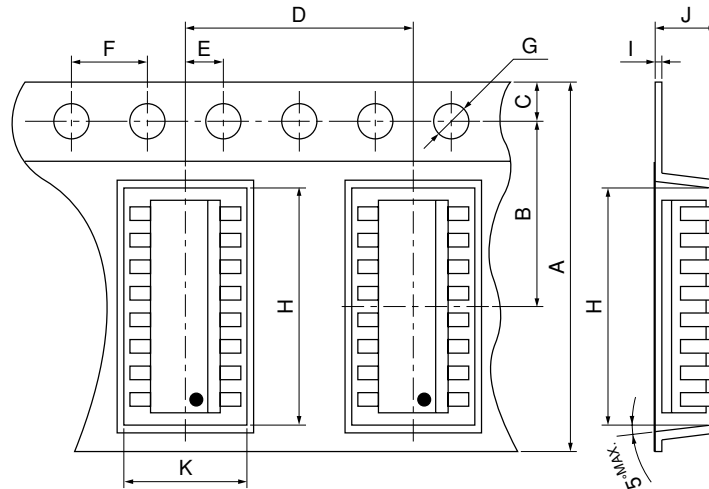
Package materials

Carrier tape : PS

Cover tape : PET (three layer system)

Reel : PS

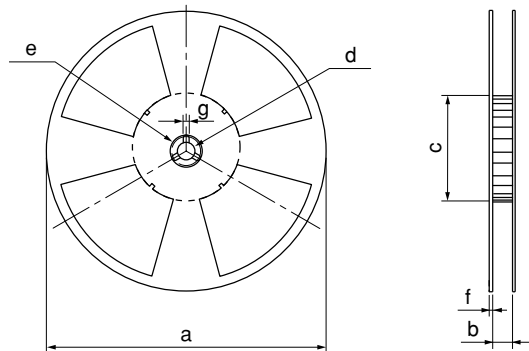
Carrier tape structure and Dimensions



Dimensions List (Unit : mm)

A	B	C	D	E	F	G
24.0 ^{+0.3}	11.5 ^{±0.1}	1.75 ^{±0.1}	12.0 ^{±0.1}	2.0 ^{±0.1}	4.0 ^{±0.1}	φ1.5 ^{+0.1} ₀
H	I	J	K			
10.8 ^{±0.1}	0.4 ^{±0.05}	3.0 ^{±0.1}	7.4 ^{±0.1}			

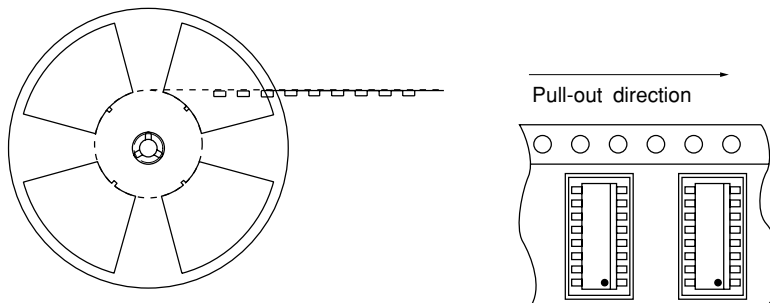
Reel structure and Dimensions



Dimensions List (Unit : mm)

a	b	c	d
330	25.5 ^{±1.5}	100 ^{±1.0}	13 ^{±0.5}
e	f	g	
23 ^{±1.0}	2.0 ^{±0.5}	2.0 ^{±0.5}	

Direction of product insertion



[Packing : 1 000pcs/reel]

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(i) The devices in this publication are designed for use in general electronic equipment designs such as:

- Personal computers
- Office automation equipment
- Telecommunication equipment [terminal]
- Test and measurement equipment
- Industrial control
- Audio visual equipment
- Consumer electronics

(ii) Measures such as fail-safe function and redundant design should be taken to ensure reliability and safety when SHARP devices are used for or in connection

with equipment that requires higher reliability such as:

- Transportation control and safety equipment (i.e., aircraft, trains, automobiles, etc.)
- Traffic signals
- Gas leakage sensor breakers
- Alarm equipment
- Various safety devices, etc.

(iii) SHARP devices shall not be used for or in connection with equipment that requires an extremely high level of reliability and safety such as:

- Space applications
- Telecommunication equipment [trunk lines]
- Nuclear power control equipment
- Medical and other life support equipment (e.g., scuba).

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